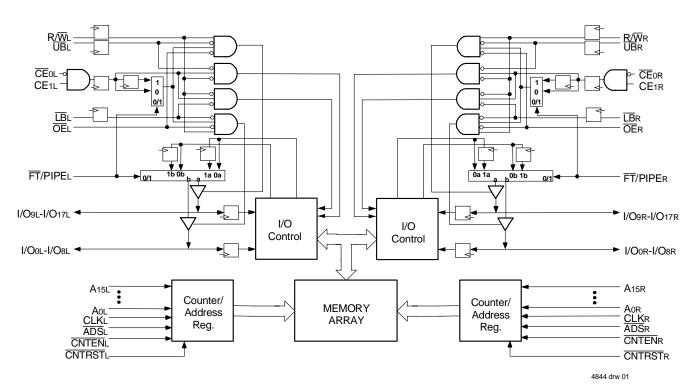


HIGH-SPEED 64K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

Features

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- * High-speed clock to data access
 - Commercial: 7.5/9/12ns (max.)
 - Industrial: 9ns (max.)
- Low-power operation
 - IDT709389L
 - Active: 1.2W (typ.)
 - Standby: 2.5mW (typ.)
- Flow-Through or Pipelined output mode on either Port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- Full synchronous operation on both ports
 - 4ns setup to clock and 0ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 7.5ns clock to data out in the Pipelined output mode
- Self-timed write allows fast cycle time
- 12ns cycle time, 83MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- TTL- compatible, single 5V (±10%) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP) package



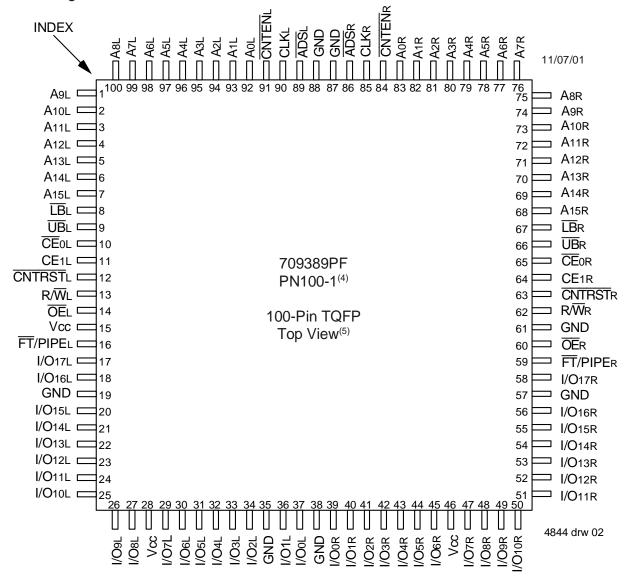
Functional Block Diagram

IDT709389L

gh-Speed 64K x 18 Synchronous Pipelined Dual-Port Static RAM

Description

The IDT709389 is a high-speed 64K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT709389 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{CE}o$ and CE_1 , permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 1.2W of power.



Pin Configurations^(1,2,3)

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground.
- 3. Package body is approximately 14mm x 14mm x 1.4mm
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names		
CEOL, CE1L	CEOR, CE1R	Chip Enables		
R/WL	R/WR	Read/Write Enable		
OEL	0 Er	Output Enable		
Aol - A15l	A0R - A15R	Address		
I/O0L - I/O17L	I/O0r - I/O17r	Data Input/Output		
CLKL	CLKR	Clock		
ŪBL	ŪBR	Upper Byte Select		
L BL	LB R	Lower Byte Select		
ĀDĪSL	ADSR	Address Strobe		
	<u>CNTEN</u> R	Counter Enable		
CNTRST L		Counter Reset		
FT/PIPEL	FT /PIPER	Flow-Through/Pipeline		
V	cc	Power		
G	ND	Ground		

4844 tbl 01

Truth Table I-Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	Ē₽	CE1	ŪB	ЕВ	R/W	Upper Byte I/O9-17	Lower Byte I/O0-8	Mode
Х	↑	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	\uparrow	Х	L	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	\uparrow	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	\uparrow	L	Н	L	Н	L	DATAIN	High-Z	Write to Upper Byte Only
Х	\uparrow	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only
Х	\uparrow	L	Н	Г	L	L	DATAIN	DATAIN	Write to Both Bytes
L	\uparrow	L	Н	Ц	Н	Н	DATAOUT	High-Z	Read Upper Byte Only
L	\uparrow	L	Н	н	L	Н	High-Z	DATAOUT	Read Lower Byte Only
L	\uparrow	L	Н	L	L	Н	DATAOUT	DATAOUT	Read Both Bytes
Н	Х	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTES: 1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. \overrightarrow{ADS} , \overrightarrow{CNTEN} , \overrightarrow{CNTRST} = X.

3. \overline{OE} is an asynchronous input signal.

4844 tbl 02

High-Speed 64K x 18 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Truth Table II—Address Counter Control^(1,2,6)

Address	Previous Address	Addr Used	CLK	ADS	CNTEN	CNTRST	I/O ⁽³⁾	Mode
Х	Х	0	Ŷ	Х	Х	L	Dvo(0)	Counter Reset to Address 0
An	Х	An	Ŷ	L ⁽⁴⁾	Х	Н	Dl∕O(n)	External Address Utilized
An	Ap	Ap	Ŷ	Н	Н	Н	DVO(p)	External Address Blocked—Counter Disabled (Ap reused)
Х	Ap	Ap + 1	Ŷ	Н	L ⁽⁵⁾	Н	DI/O(p+1)	Counter Enable—Internal Address Generation

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{CE}_{0} , \overline{LB} , \overline{UB} , and $\overline{OE} = V_{1L}$; CE_{1} and $R/\overline{W} = V_{1H}$.

3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.

4. ADS is independent of all other signals including CE0, CE1, UB and LB.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CEo, CE1, UB and LB.

6. While an external address is being loaded (ADS = VIL), R/W = VIH is recommended to ensure data is not written arbitrarily.

Recommended Operating Recommer Temperature and Supply Voltage Conditions

Grade	Ambient Temperature ⁽²⁾	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	۷
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2		6.0(1)	V
VIL	Input Low Voltage	-0.5(2)		0.8	V

NOTES:

4844 tbl 04

mΑ

4844 tbl 06

1. VTERM must not exceed Vcc + 10%.

2. VIL \geq -1.5V for pulse width less than 10ns.

Absolute Maximum Ratings⁽¹⁾ Symbol Rating Commercial Unit & Industrial VTERM⁽²⁾ Terminal Voltage -0.5 to +7.0 ۷ with Respect to GND TBIAS °C Temperature -55 to +125 Under Bias TSTG °C Storage -65 to +150 Temperature

Capacitance⁽¹⁾

$(TA = +25 \degree C, f = 1.0 MH)$	z)
------------------------------------	----

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit		
CIN	Input Capacitance	VIN = 3dV	9	pF		
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF		

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

NOTES:

Ιουτ

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

50

DC Output

Current

 VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%. 4844 tbl 03

4844 tbl 05

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range ($Vcc = 5.0V \pm 10\%$)

				709389L		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit	
lLıl	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, V $\!$	_	5	μA	
ILOI	Output Leakage Current	$\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{CC}$	_	5	μA	
Vol	Output Low Voltage	lo∟ = +4mA	_	0.4	V	
Vон	Output High Voltage	юн = -4mA	2.4	1	V	
					4844 tbl 08	

NOTE:

1. At $Vcc \le 2.0V$ input leakages are undefined.

DC Electrical Characteristics Over the Operating

Temperature and Supply Voltage Range⁽³⁾ ($Vcc = 5V \pm 10\%$)

						89L7 Only	7093 Coi & I	m'l	70938 Com'l		
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Max.	Unit
ICC	Dynamic Operating Current	CEL and CER= V⊫ Outputs Disabled	COM'L	L	275	465	250	400	230	355	mA
	(Both Ports Active)	$f = fMAX^{(1)}$	IND	L			300	430			
ISB1	Standby Current (Both Ports - TTL	$\overline{CEL} = \overline{CER} = VIH$	COM'L	L	95	150	80	135	70	110	mA
	Level Inputs)	$f = fMAX^{(1)}$	IND	L			95	160			
ISB2	ISB2 Standby Current (One Port - TTL Level Inputs)	ne Port - TTL CE"B" = VH ⁽³⁾	COM'L	L	200	295	175	275	150	240	mA
			IND	L			195	295			
ISB3	Full Standby Current	Both Ports CER and	COM'L	L	0.5	3.0	0.5	3.0	0.5	3.0	mA
	(Both Ports - CMOS Level Inputs)	$ \overline{CEL} \ge VCC - 0.2V VN \ge VCC - 0.2V or VN \le 0.2V, f = 0(2) $	IND	L			0.5	6.0			
ISB4	Full Standby Current	\overline{CE} "A" < 0.2V and	COM'L	L	190	290	170	270	140	225	mA
(One Port - CMOS Level Inputs)		$ \begin{array}{l} \overline{C}\overline{E}^{*}B^{*} \stackrel{>}{\geq} VCC - 0.2V^{(5)} \\ V\mathbb{N} \stackrel{>}{\geq} VCC - 0.2V \text{ or} \\ V\mathbb{N} \stackrel{<}{\leq} 0.2V, \text{ Active Port} \\ Outputs Disabled, f = fMAX^{(1)} \end{array} $	IND	L		_	190	290			
	8	•			•		•		•	• 4	844 tbl 0

NOTES:

 At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. Vcc = 5V, TA = $25^{\circ}C$ for Typ, and are not production tested. Icc pc(f=0) = 150mA (Typ).

5. CEx = VIL means \overline{CE}_{0X} = VIL and CE1X = VIH

CEx = VIH means $\overline{CE_{0x}}$ = VIH or CE1x = VIL

 $CEx \le 0.2V$ means $\overline{CE}_{0x} \le 0.2V$ and $CE_{1x} \ge Vcc - 0.2V$

 $CEx \geq Vcc$ - 0.2V means $\overline{CE} \textsc{ox} \geq Vcc$ - 0.2V or $CE1x \leq 0.2V$

"X" represents "L" for left port or "R" for right port.

IDT709389L

igh-Speed 64K x 18 Synchronous Pipelined Dual-Port Static RAI

vial and Commercial Temperature Pa

5V

893Ω

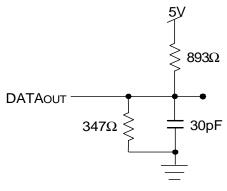
5pF*

4844 drw 05

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

4844 tbl 10





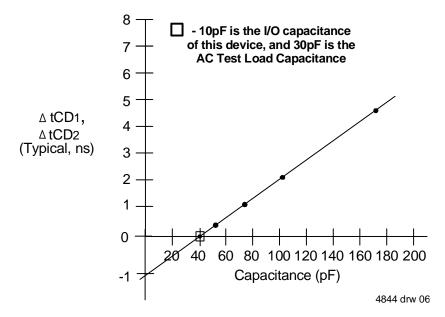
DATAOUT

4844 drw 04

Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcкьz, tcкнz, toьz, and toнz). *Including scope and jig.

 $347\Omega \leq$





AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ (Vcc = $5V \pm 10\%$, TA = $0^{\circ}C$ to $+70^{\circ}C$)

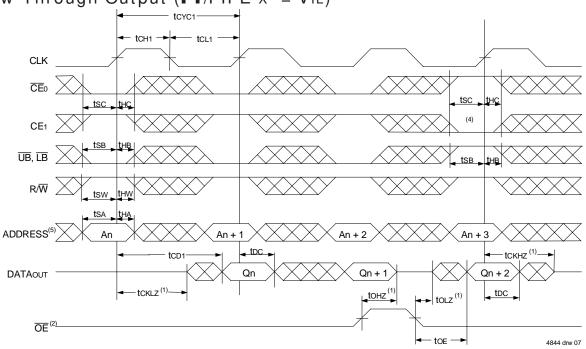
			389L7 I Only	Co	889L9 om'l Ind	709389L12 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tCYC1	Clock Cycle Time (Flow-Through) ⁽²⁾	22		25	_	30		ns
tCYC2	Clock Cycle Time (Pipelined) ⁽²⁾	12		15	_	20	—	ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	7.5	_	12	_	12	—	ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	7.5		12	_	12		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	5	_	6		8	—	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	5	—	6	_	8	—	ns
tR	Clock Rise Time		3		3		3	ns
tr	Clock Fall Time		3		3		3	ns
tSA	Address Setup Time	4		4		4		ns
tHA	Address Hold Time	0		1		1		ns
tsc	Chip Enable Setup Time	4		4		4		ns
tHC	Chip Enable Hold Time	0		1		1		ns
tsв	Byte Enable Setup Time	4		4		4		ns
tнв	Byte Enable Hold Time	0		1		1		ns
tsw	R/W Setup Time	4		4		4		ns
tHW	R/W Hold Time	0		1		1		ns
tsp	Input Data Setup Time	4		4		4		ns
tHD	Input Data Hold Time	0		1		1		ns
tsad	ADS Setup Time	4		4	_	4		ns
thad	ADS Hold Time	0		1		1		ns
tSCN	CNTEN Setup Time	4		4		4		ns
tHCN	CNTEN Hold Time	0		1		1		ns
tSRST	CNTRST Setup Time	4		4		4		ns
tHRST	CNTRST Hold Time	0		1		1		ns
tOE	Output Enable to Data Valid		9		12		12	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2		2		ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		18		20		25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		7.5		9		12	ns
tDC	Data Output Hold After Clock High	2		2		2		ns
tскнz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tCKLZ	Clock High to Output Low-Z ⁽¹⁾	2		2		2		ns
Port-to-Port		1		1	<u>n</u>	1		
tCWDD	Write Port Clock High to Read Data Delay		28		35		40	ns
tocs	Clock-to-Clock Setup Time	1	10		15		15	ns

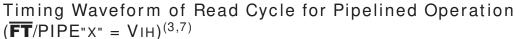
1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

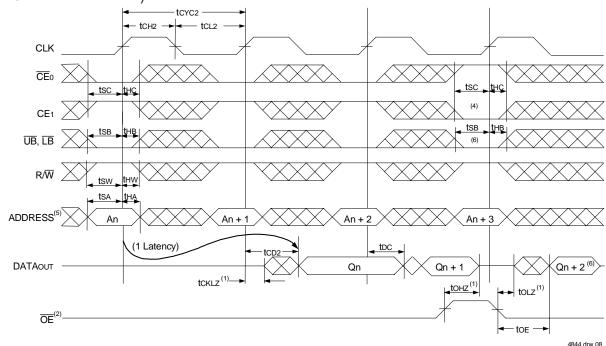
2. The Pipelined output parameters (tcvc2, tcD2) to either the Left or Right ports when FT/PIPE = VIH. Flow-Through parameters (tcvc1, tcD1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER and FT/PIPEL.



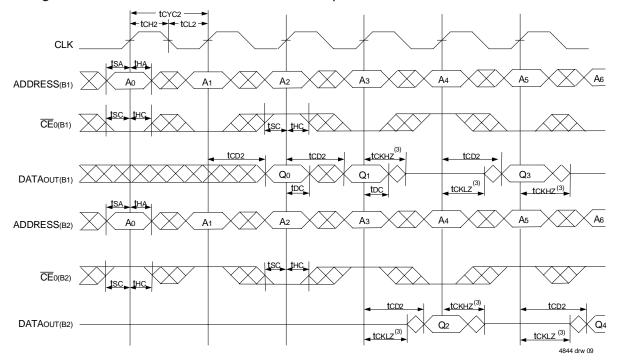




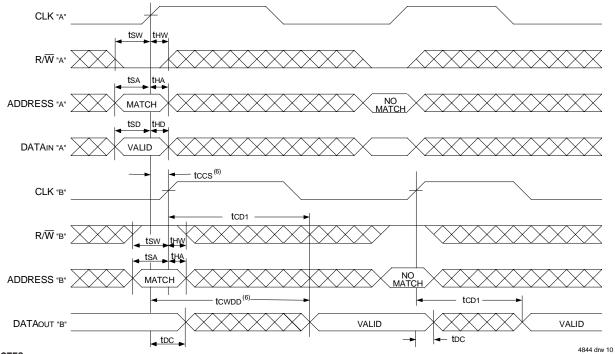


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{\text{ADS}} = \text{ViL}, \overline{\text{CNTEN}} \text{ and } \overline{\text{CNTRST}} = \text{ViH}.$
- The output is disabled (High-Impedance state) by CE₀ = VIH, CE1 = VIL, UB = VIH, or LB = VIH following the next rising edge of the clock. Refer to Truth Table 1.
 Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 6. If UB or LB was HIGH, then the Upper Byte and/or Lower Byte of DATAOUT for Qn + 2 would be disabled (High-Impedance state).
- 7. "X" here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)

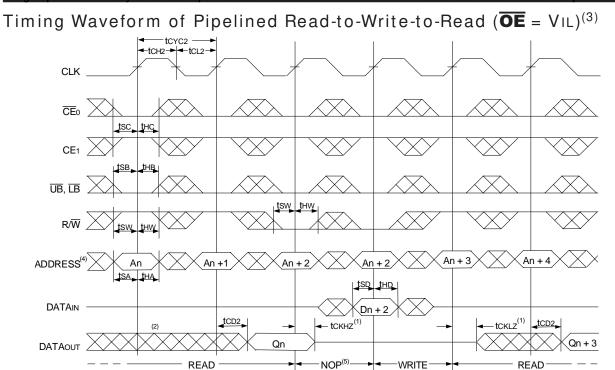


Timing Waveform of Write with Port-to-Port Flow-Through Read^(4,5,7)

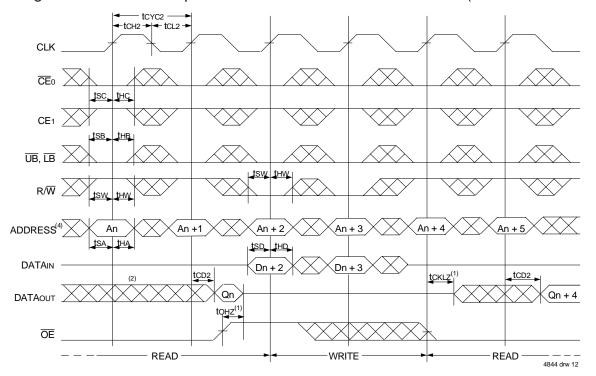


- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT709389 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; CE_1 , \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 5. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

4844 drw 11

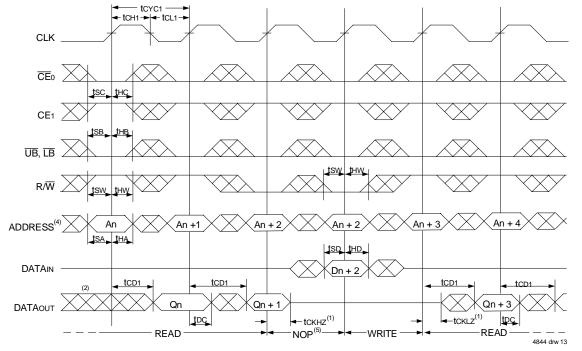


Timing Waveforn of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

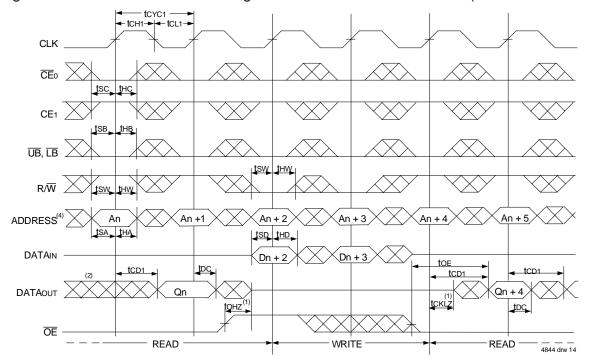


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. CE0, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾

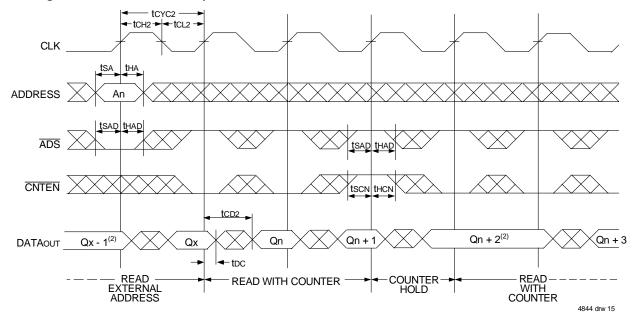


Timing Waveform of Flow -Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

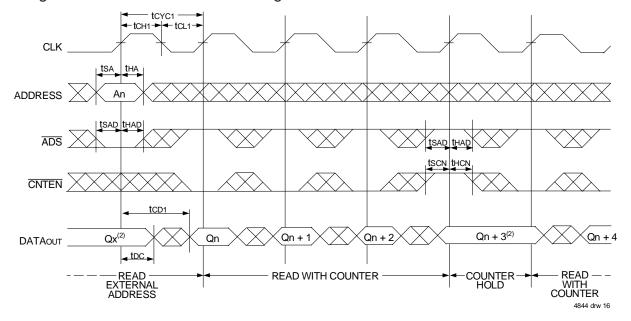


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance is determined by the previous cycle control signals.
- 3. CE0, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

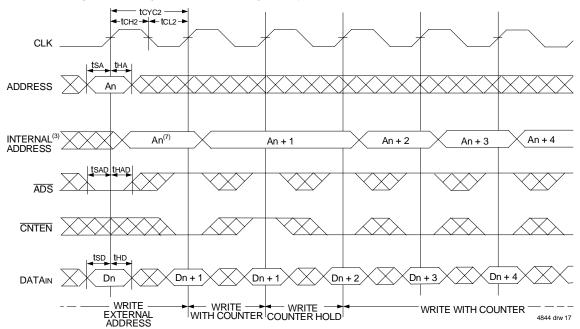


 $Timing\ Waveform\ of\ Flow\ -Through\ Read\ with\ Address\ Counter\ Advance^{(1)}$

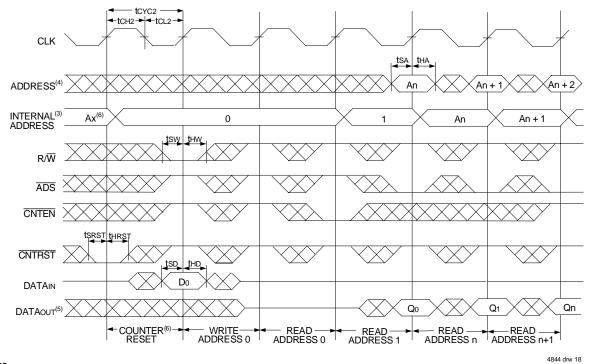


- 1. \overline{CE}_{0} , \overline{OE} , \overline{UB} , and $\overline{LB} = VIL$; CE1, R/W, and $\overline{CNTRST} = VIH$.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow -Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)⁽²⁾



NOTES:

1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.

- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- Addresses do not have to be accessed sequentially since ADS = Vi∟ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
 Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

^{2.} \overline{CE}_0 , \overline{UB} , $\overline{LB} = V_{1L}$; $CE_1 = V_{1H}$.

IDT709389L

h-Speed 64K x 18 Synchronous Pipelined Dual-Port Static RAN

A Functional Description

The IDT709389 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

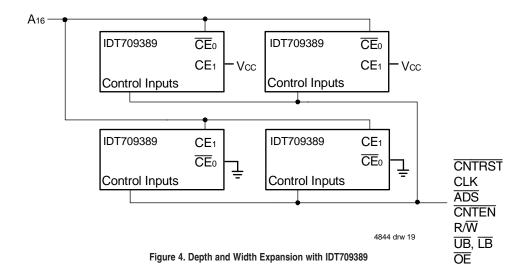
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

 $\overline{CE}_0 = VIH$ or $CE_1 = VIL$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT709389's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{CE}_0 = VIL$ and $CE_1 = VIH$ to reactivate the outputs.

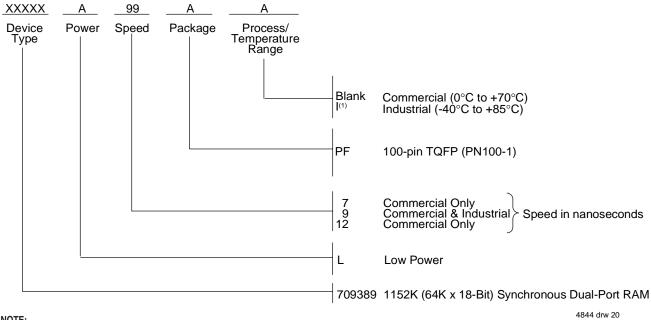
Depth and Width Expansion

The IDT709389 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The 709389 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.



Ordering Information



NOTE:

1. Industrial temperature range is available.

For specific speeds, packages and powers contact your sales office.

Datasheet Document History

9/30/99:	Initial Public Release								
11/10/99:	Replaced IDT logo								
12/22/99:	Page 1 Added missing diamond								
1/10/01:	Page 4	Changed information in Truth Table II							
		Increased storage temperature parameter							
		Clarified TA parameter							
	Page 5	DC Electrical parameters-changed wording from "open" to "disabled"							
	Changed ±200mV to 0mV in notes								
	Removed Preliminary status								
10/18/01:	Page 2 A	dded date revision for pin configuration							
	Page 5 &	7 Added Industrial temp to column heading and values for 9ns speed to DC & AC Electrical Characteristics							
	Page 15	Added Industrial temp offering to 9ns ordering information							
	Page 4, 5 & 7 Removed Industrial temp footnote from all tables								
	Page 1 & 15 Replace ™ logo with ® logo								
01/29/09:	Page 15	Removed "IDT" from orderable part number							



CORPORATE HEADQUARTERS 6024 Silver Creek Valley Road San Jose, CA 95138

for SALES: 800-345-7015 or 408-284-8200 fax: 408-284-2775 www.idt.com

for Tech Support: 408-284-2794 DualPortHelp@idt.com

The IDT logo is a registered trademark of Integrated Device Technology, Inc.